Title (en)

SEMICONDUCTOR LAYER SEQUENCE AND METHOD FOR PRODUCING THE SAME

Title (de)

HALBLEITERSCHICHTENFOLGE UND VERFAHREN ZU DEREN HERSTELLUNG

Title (fr)

SUCCESSION DE COUCHES DE SEMI-CONDUCTEURS ET PROCÉDÉ DE FABRICATION DE CELLE-CI

Publication

EP 3069389 A1 20160921 (DE)

Application

EP 14799686 A 20141104

Priority

- DE 102013112490 A 20131113
- EP 2014073717 W 20141104

Abstract (en)

[origin: WO2015071134A1] In at least one embodiment, the semiconductor layer sequence (10) has an n-conducting n side (11), a p-conducting p side (13) and an active zone (2) lying in between. The active zone (2) has at least one radiation-active layer (21) with a first material composition for generating a first radiation (L1). The at least one radiation-active layer (21) is oriented perpendicularly to a direction of growth (z) of the semiconductor layer sequence. Furthermore, the active zone (2) has a multiplicity of radiation-active tubes (22) with a second material composition or a different crystal structure for generating a second radiation (L2), wherein the second material composition is different from the first material composition. The radiation-active tubes (22) are oriented parallel to the direction of growth (z).

IPC 8 full level

H01L 33/00 (2010.01); **H01L 33/02** (2010.01); **H01L 33/08** (2010.01)

CPC (source: EP US)

H01L 33/0062 (2013.01 - EP US); **H01L 33/025** (2013.01 - EP US); **H01L 33/06** (2013.01 - US); **H01L 33/08** (2013.01 - EP US); **H01L 33/30** (2013.01 - US)

Citation (search report)

See references of WO 2015071134A1

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)

BA ME

DOCDB simple family (publication)

DE 102013112490 A1 20150513; EP 3069389 A1 20160921; JP 2017501565 A 20170112; JP 6284638 B2 20180228; US 2016276531 A1 20160922; US 9653646 B2 20170516; WO 2015071134 A1 20150521

DOCDB simple family (application)

DE 102013112490 A 20131113; EP 14799686 A 20141104; EP 2014073717 W 20141104; JP 2016530876 A 20141104; US 201415034565 A 20141104